NSN 5961-01-581-5270

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-581-5270

Special Features:

Shelf Life:

A110a0

20 mj avalanche energy guaranteed; ultrafast 75 nanosecond recovery time; 175 degree celsius operating junction temperature; to-220
package; epoxy meets ul94 v-0 at 0.125 inches; low forward voltage; low leakage current; high temperature glass passivated junction;
reverse voltage to 1000 v

N/a
Unit Of Measure:
Demilitarization:
No
Fiig: